

**Amendments to the Claims:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

**Listing of Claims:**

Claim 1 (original): A silicon capacitor formed on an integrated circuit substrate, comprising:

    a metal portion on the substrate;

    a silicon nitride (SiN) portion sputtered on the substrate; and

    a silicon (Si) portion sputtered on the silicon nitride portion.

Claim 2 (original): The silicon capacitor of claim 1, wherein the silicon nitride decreases leakage.

Claim 3 (original): The silicon capacitor of claim 1, further comprising a second silicon nitride portion.

Claim 4 (original): The silicon capacitor of claim 1, further comprising a second metal portion.

Claim 5 (original): The silicon capacitor of claim 1, wherein the capacitor is formed using a process including:

    depositing metal on the substrate;

    sputtering silicon with nitrogen gas to form SiN;

    removing nitrogen gas flow to deposit pure silicon;

    adding nitrogen gas again to cap the layer with SiN; and

    depositing metal.

Claim 6 (original): The silicon capacitor of claim 5, wherein each layer deposited is approximately forty angstroms thick.

Claims 7-14 (cancel)